



ALPHA & OMEGA
SEMICONDUCTOR

AON6236

40V N-Channel MOSFET

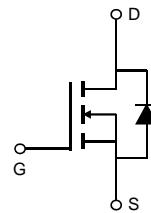
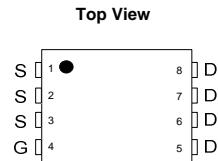
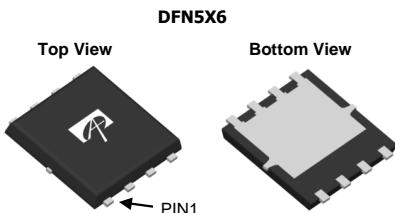
General Description

The AON6236 uses trench MOSFET technology that is uniquely optimized to provide the most efficient high frequency switching performance. Power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and C_{rss} . In addition, switching behavior is well controlled with a "Schottky style" soft recovery body diode.

Product Summary

V_{DS}	40V
I_D (at $V_{GS}=10V$)	30A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 7mΩ
$R_{DS(ON)}$ (at $V_{GS} = 4.5V$)	< 10.5mΩ

100% UIS Tested
100% R_g Tested



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^G	I_D	30	A
$T_C=100^\circ C$		24	
Pulsed Drain Current ^C	I_{DM}	120	
Continuous Drain Current	I_{DSM}	19	A
$T_A=70^\circ C$		15	
Avalanche Current ^C	I_{AS}	33	A
Avalanche energy L=0.1mH ^C	E_{AS}	54	mJ
Power Dissipation ^B	P_D	39	W
$T_C=100^\circ C$		15.5	
Power Dissipation ^A	P_{DSM}	4.2	W
$T_A=70^\circ C$		2.7	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	24	30	°C/W
Maximum Junction-to-Ambient ^{A,D}		53	64	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	2.6	3.2	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	40			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=40\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm20\text{V}$			±100	nA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.4	1.85	2.4	V
$I_{\text{D(ON)}}$	On state drain current	$V_{GS}=10\text{V}, V_{DS}=5\text{V}$	120			A
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=20\text{A}$ $T_J=125^\circ\text{C}$		5.6 8.4	7 10.5	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=20\text{A}$		8	10.5	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}, I_D=20\text{A}$		80		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.72	1	V
I_S	Maximum Body-Diode Continuous Current ^G				30	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=20\text{V}, f=1\text{MHz}$		1225		pF
C_{oss}	Output Capacitance			318		pF
C_{rss}	Reverse Transfer Capacitance			26.5		pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		1.7	3.0	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}, V_{DS}=20\text{V}, I_D=20\text{A}$		18.5	26	nC
$Q_g(4.5\text{V})$	Total Gate Charge			8.2	12	nC
Q_{gs}	Gate Source Charge			3.5		nC
Q_{gd}	Gate Drain Charge			2.5		nC
$t_{\text{D(on)}}$	Turn-On Delay Time	$V_{GS}=10\text{V}, V_{DS}=20\text{V}, R_L=1\Omega, R_{\text{GEN}}=3\Omega$		6		ns
t_r	Turn-On Rise Time			2.8		ns
$t_{\text{D(off)}}$	Turn-Off Delay Time			23.5		ns
t_f	Turn-Off Fall Time			3		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=20\text{A}, dI/dt=500\text{A}/\mu\text{s}$		14		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=20\text{A}, dI/dt=500\text{A}/\mu\text{s}$		32.5		nC

A. The value of R_{thJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on R_{thJA} and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.

B. The power dissipation P_b is based on $T_{J(\text{MAX})}=150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.

D. The R_{thJA} is the sum of the thermal impedance from junction to case R_{thJC} and case to ambient.

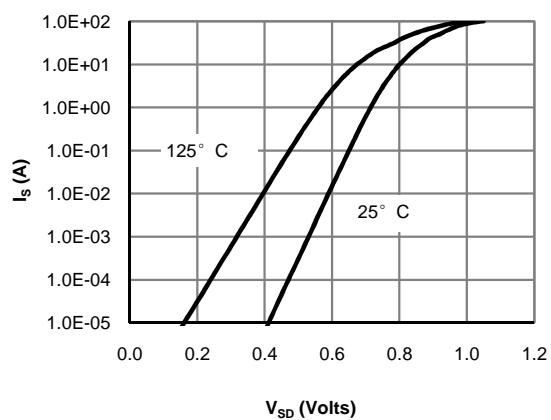
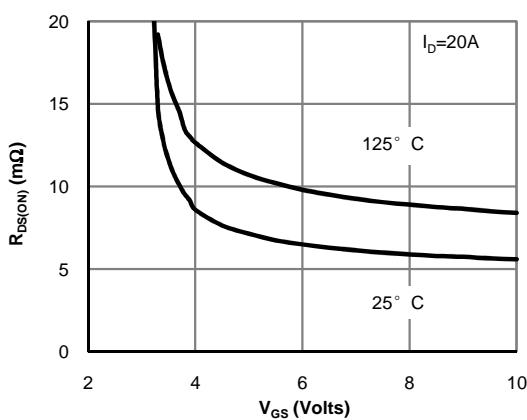
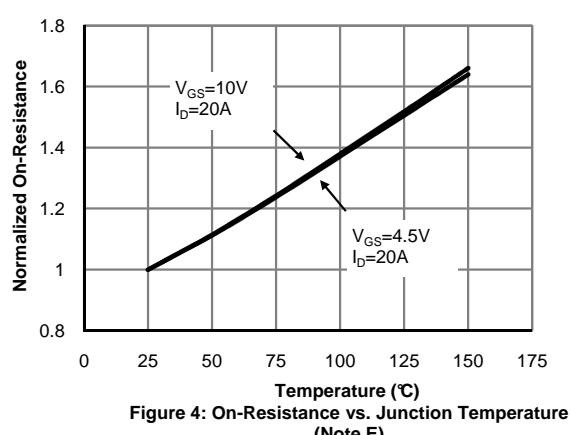
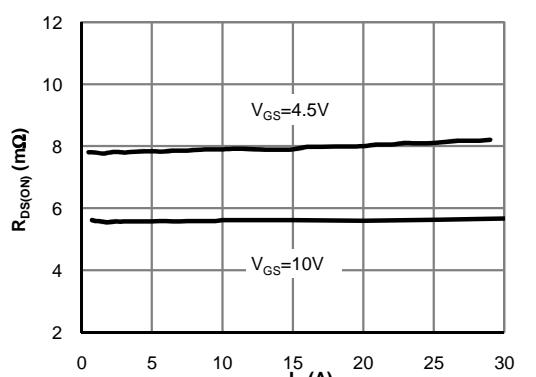
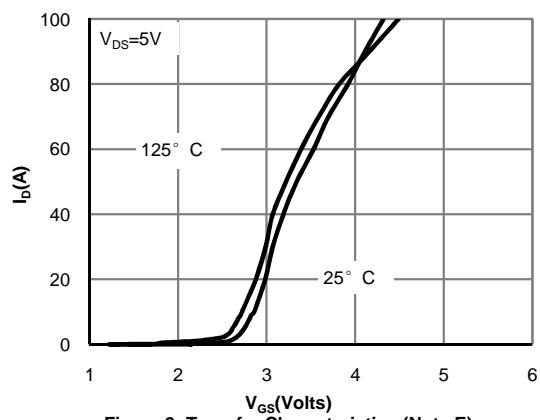
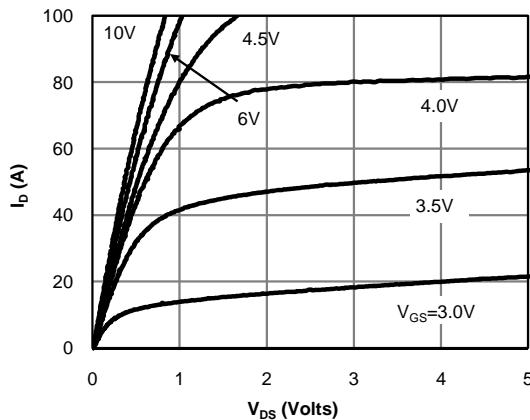
E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

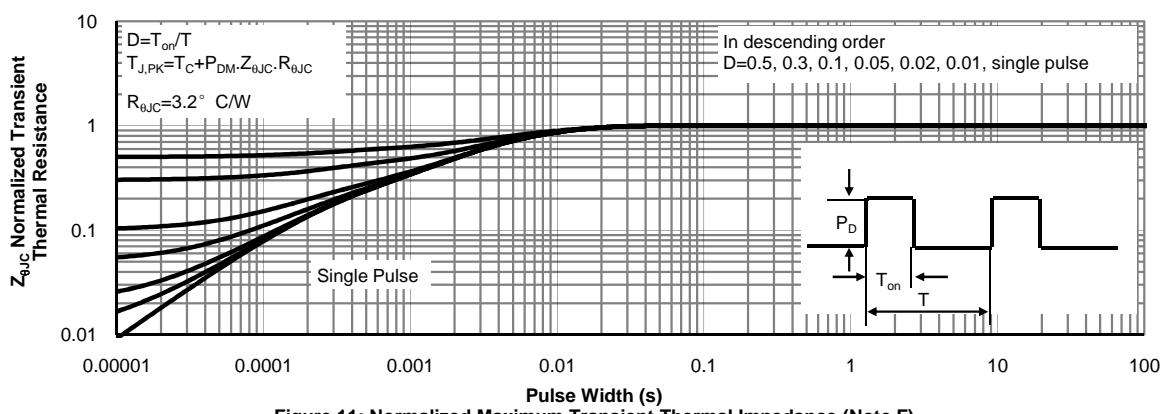
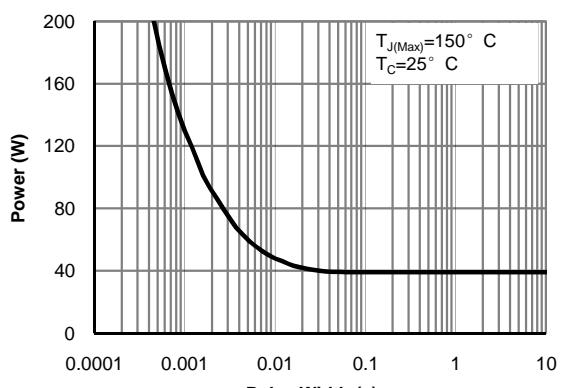
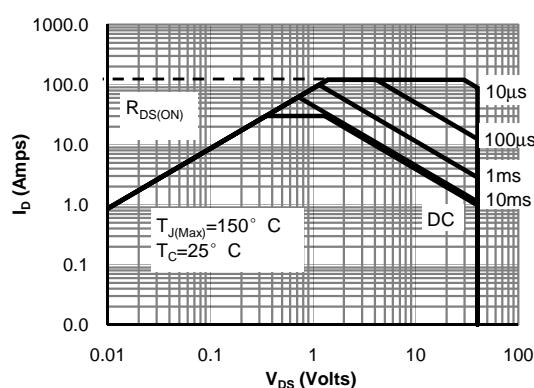
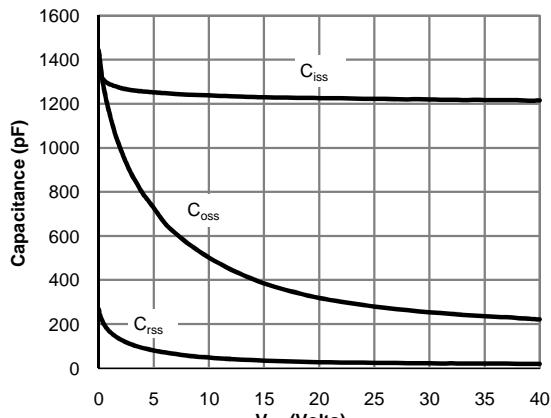
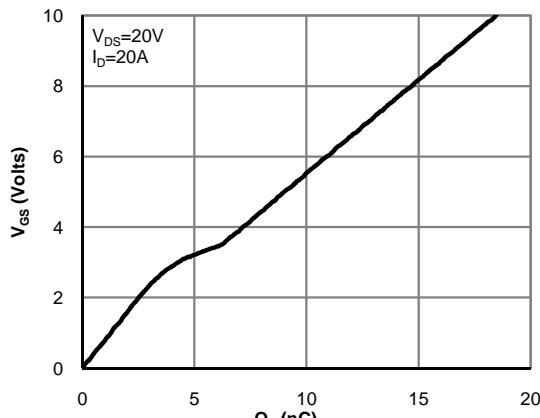
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(\text{MAX})}=150^\circ\text{C}$. The SOA curve provides a single pulse rating.

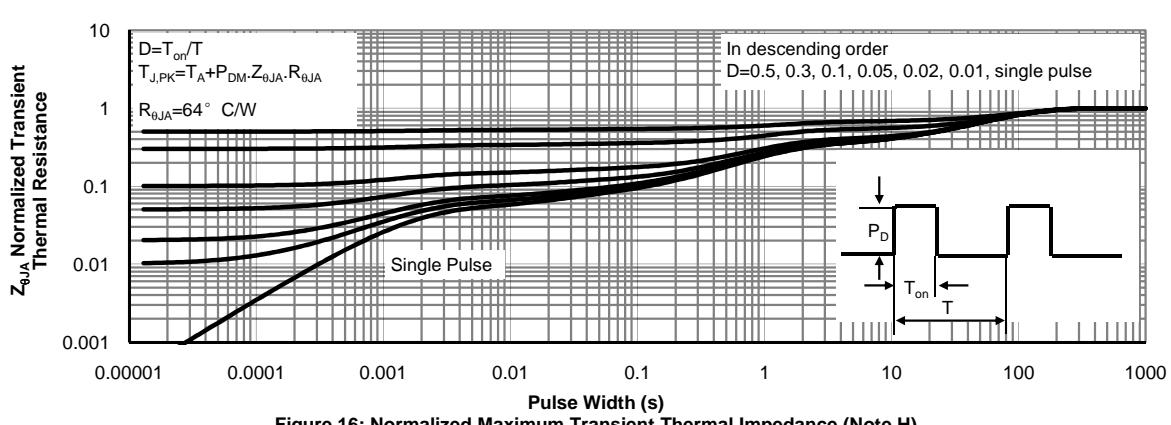
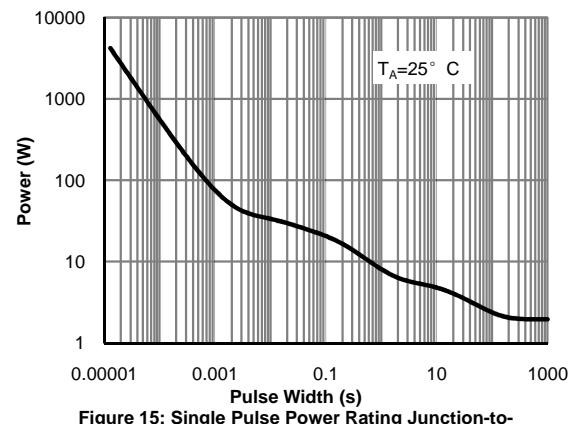
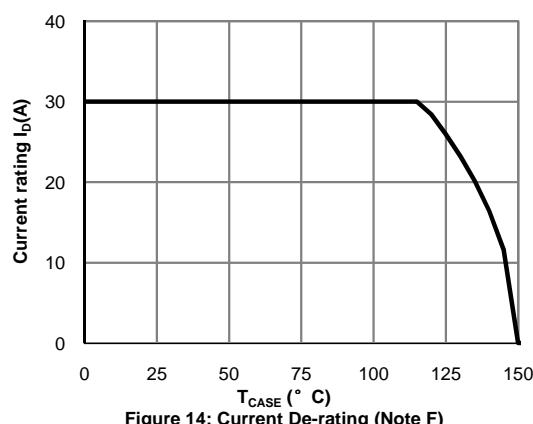
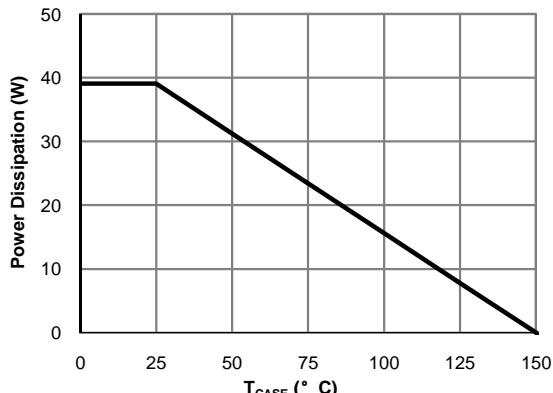
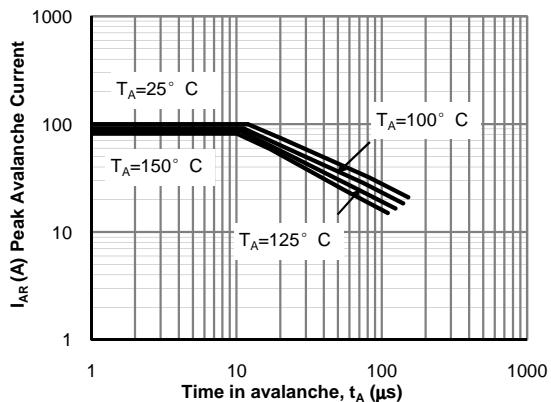
G. The maximum current rating is package limited.

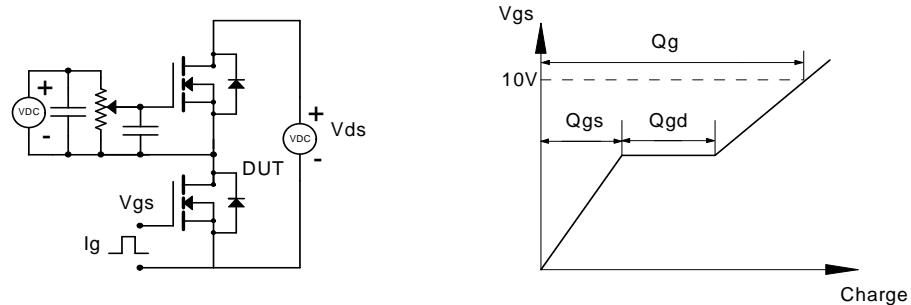
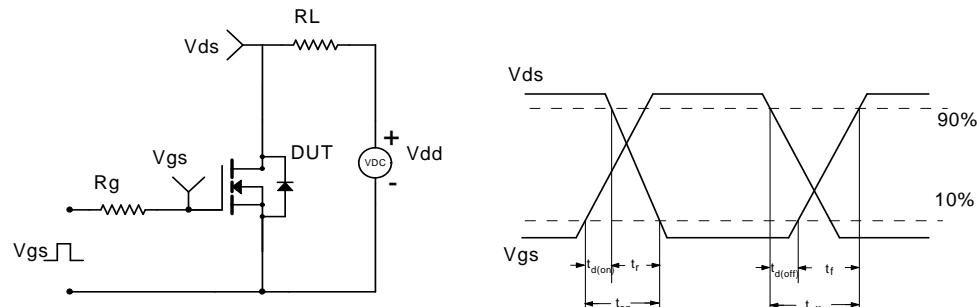
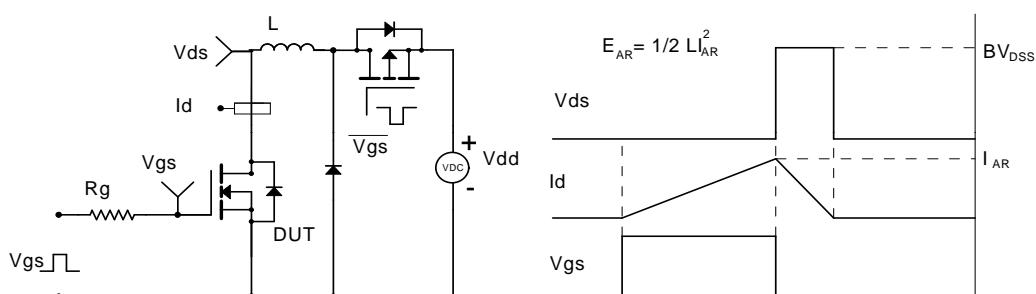
H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS


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